

2-Cell Lithium-Ion/Polymer Protector

Features

- High accuracy voltage detection circuit
 - Over-charge detection : ±25mV
 - Over-discharge detection : ±80mV
 - Discharge over-current-1 detection : ±10%
 - Discharge over-current-2 detection : ±10%
 - Load short-circuiting detection : ±10%
 - Charge over-current detection : ±8mV/±10mV
- High withstand voltage
 - Absolute maximum rating: 30V
 - Operating voltage range: 3.5V to 12V
- Low power consumption
 - Supply current: 6.6uA max. (Ta=+25°C)
- Delay times of over-charge, load short-circuiting are generated by an internal circuit (fixed).
- Delay times of over-discharge, discharge over-current-1 and 2 are controlled by external capacitors.
- Built-in breaking wire detector function
- Package: 10 pin SOP
- Lead-free, Sn 100%, Halogen-free

Applications

- Lithium-ion rechargeable battery pack
- Lithium-polymer rechargeable battery pack
- Lithium-iron phosphate rechargeable battery pack

Typical Application Circuit





These devices have limited build-in ESD protection. The leads must be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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Description

The NT1727 series is the 2-cell protection IC for lithium-ion/ lithium-polymer/lithium-iron phosphate rechargeable battery pack. The high accuracy voltage, current detector and delay time circuits are built in NT1727 series with state-of-the-art design and process.

The NT1727 series have three types of discharge over-current protection and one type of charge over-current protection.



Package and Pin Configurations



Pin No.	Symbol	Pin description					
1	V-	Input terminal connected to charger negative voltage. Discharge over-current and load short-circuiting release detector.					
2	CS	Input of overcurrent detection. Detected overcurrent by sense resistor between CS pin and VSS pin. Detected charger and load connection.					
3	DO	 FET gate control pin for discharging path (CMOS output) Normal mode : High Over-discharge mode : Low 					
4	CT2	Capacitor connection for over-discharge detection delay time.					
5	CT3	Capacitor connection for discharge over-current-1 and 2 detection delay time.					
6	VSS	The input terminal of the negative voltage of V1 cell. The input terminal of the ground of IC.					
7	V1	Cell V1 positive voltage and cell V2 negative voltage input pin					
8	V2	Cell V2 positive voltage input pin					
9	VDD	Power supply input pin					
10	СО	 FET gate control pin for charging path (Pch open-drain output). Normal mode : High Over-charge mode : Hi-impedance 					



Block Diagram





Ordering Information

NT1727A-XXX XX Package Type • S1: SOP-10L

— Version Code

Product version code:

Table 1: Detection threshold level

Product Name	Version Code	Package Type	Over- charge detection voltage V _{DET1} (V)	Over- charge release voltage V _{REL1}	Over- discharge detection voltage V _{DET2}	Over- discharge release voltage V _{REL2}	Discharge over- current-1 detection voltage V _{DET31} (V)	Discharge over- current-2 detection voltage V _{DET32} (V)	Charge over- current detection voltage V _{DET4}	Load short- circuiting detection voltage V _{SHORT}
NT1727A	FKA	S1	4.250	4.150	2.500	3.000	_	0.100	-0.025	0.250
NT1727A	FQA	S1	4.250	4.150	2.800	3.000	0.100	0.400	-0.100	0.600

Remark: Please contact our sales for the products with detection voltage value other than those specified above.

Table 2: Function

Product Name	Version Code	Package Type	Over-charge release condition	Over-discharge release condition	0 V battery charge function	Built-in breaking wire detector function	Delay time (Table 3)
NT1727A	FKA	S1		(a) Voltage release	Available	Yes	(1)
NT1727A	FQA	S1	voltage release	b) Charge current release	Available	Yes	(1)

Remark: For the details, please refer to the description of "Operations"

Table 3: Delay time

	Over-charge	Over-discharge	Discharge	Discharge	Load	Charge
	detection	detection	over-current-1	over-current-2	short-circuiting	over-current
Delay	delay time	delay time	detection	detection	detection	detection
time			delay time	delay time	delay time	delay time
	t _{vDET1} (s)	t _{VDET2} (s)	t _{vDET31} (ms)	t _{vDET32} (ms)	t _{short} (us)	t _{VDET4} (ms)
		(at C _{CT2} =0.1uF)		(at C _{CT3} =0.001uF)		
(4)	1	1	60	10	250	100
(1)	±30%	±50%	±50%	±50%	+60/-40%	±30%

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